

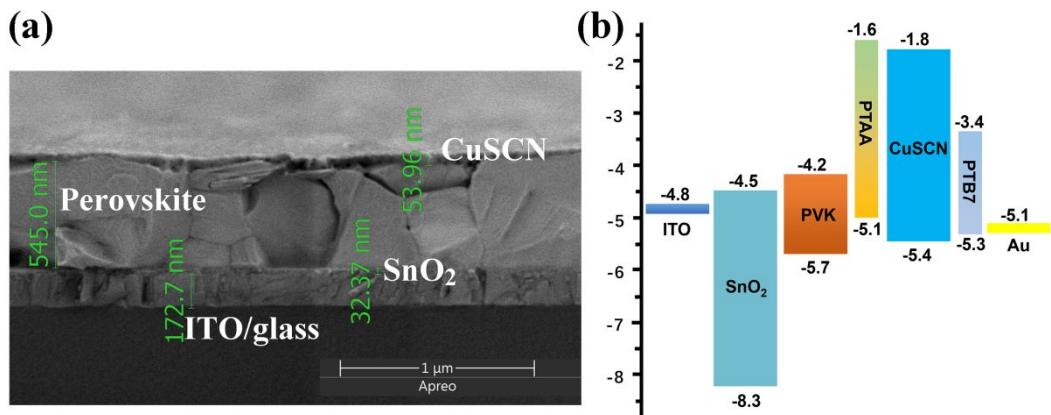
## **Supporting information**

# **Performance Promotion through Dual-Interface Engineering of CuSCN Layers in Planar Perovskite Solar Cells**

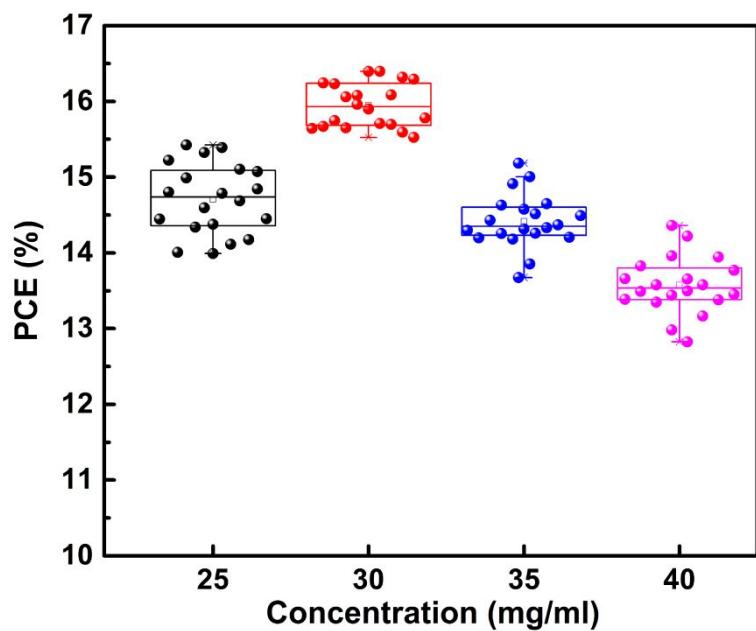
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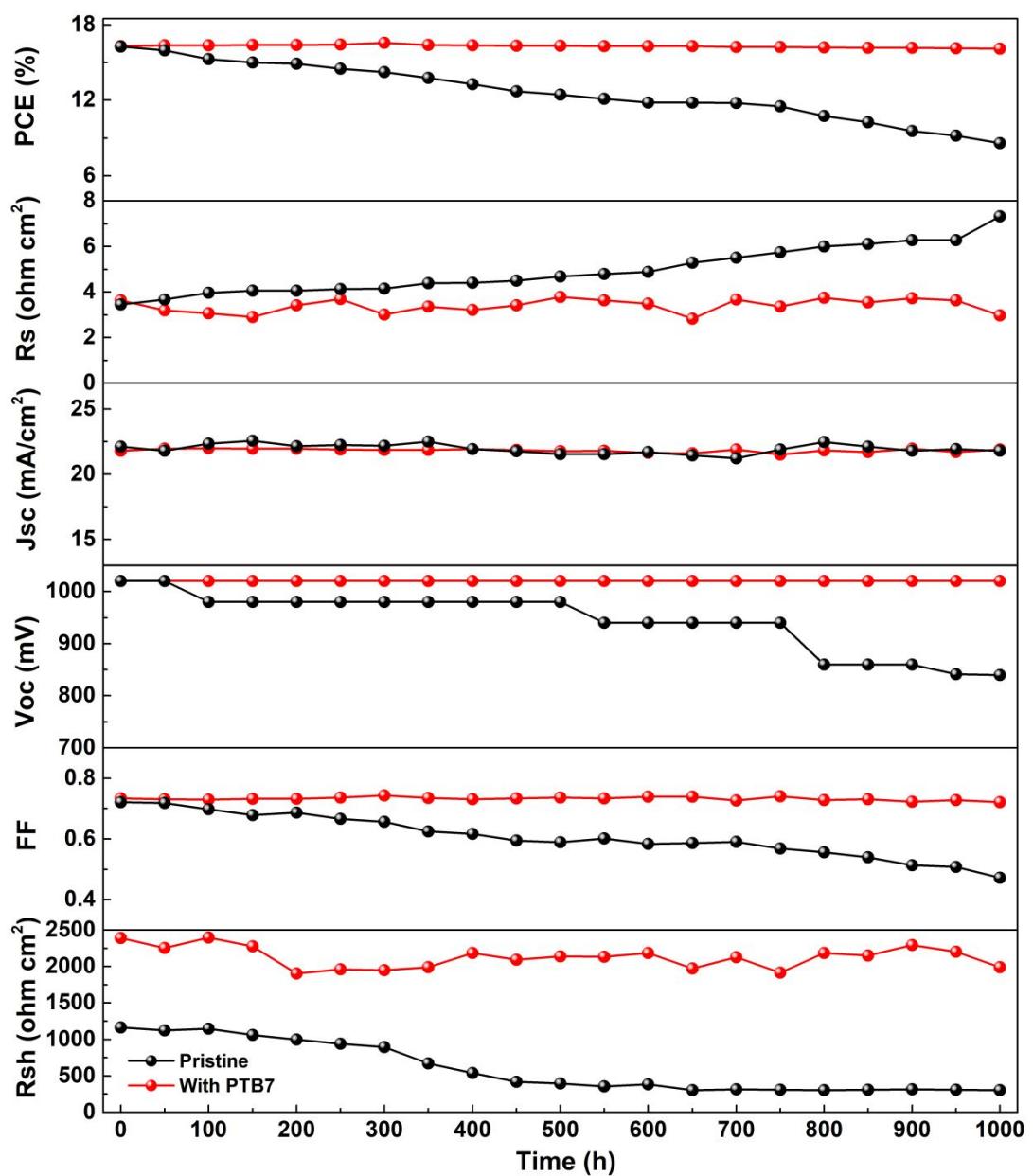
**Figure S1.** (a) Typical cross-sectional SEM image and (b) the possible band alignment of device.



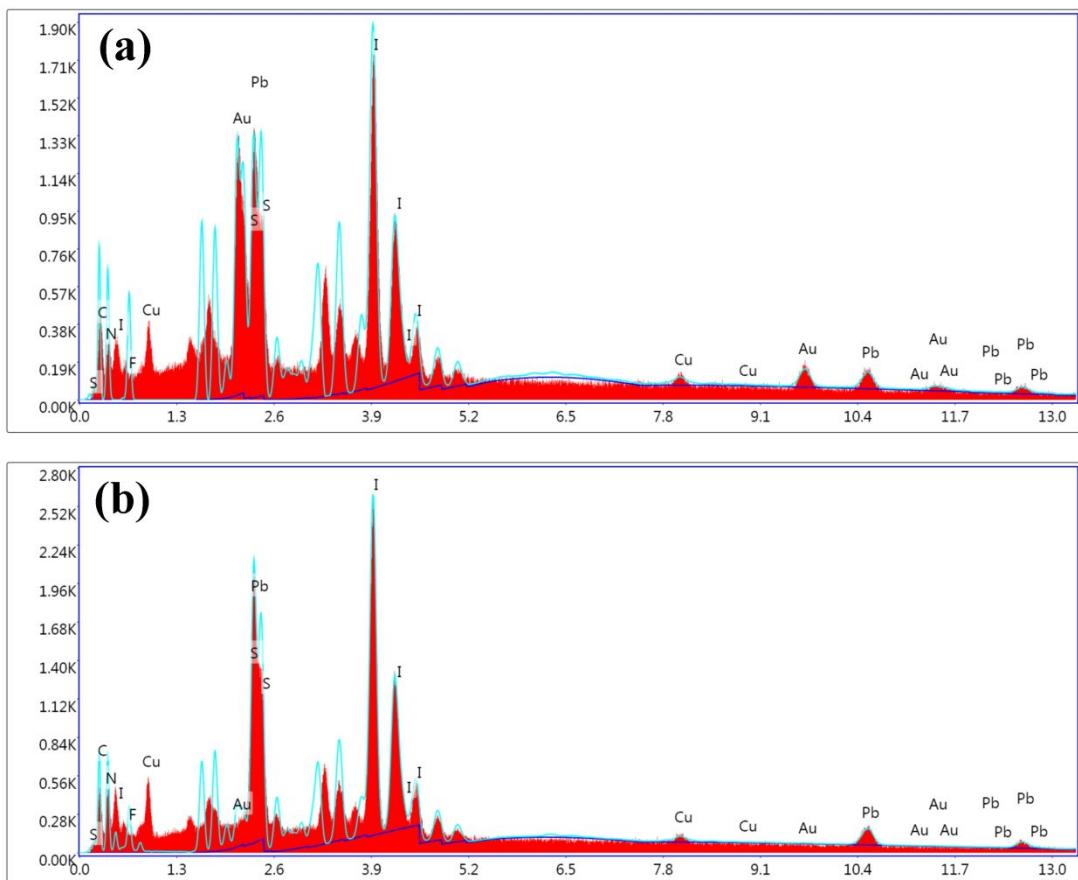
**Figure S2.** Relationship between device PCE and CuSCN concentration.

**Table S1.** Statistical photovoltaic parameters of devices fabricated with different concentration of CuSCN.

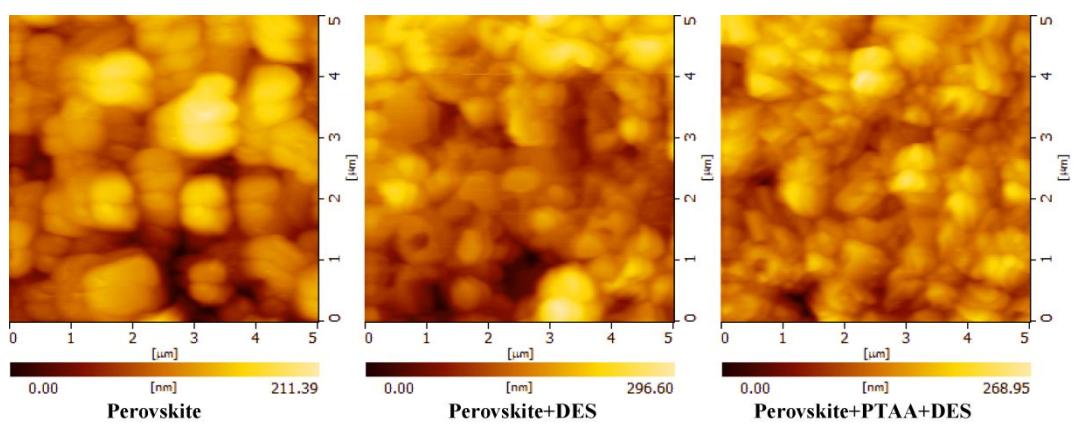
CuSCN concentration (mg/ml)	Jsc (mA/cm <sup>2</sup> )	Voc (mV)	FF (%)	PCE (%)	Rsh (Ωcm <sup>2</sup> )	Rs (Ωcm <sup>2</sup> )
25	21.37±0.40	982±9	70.1±	14.71±	1029.22±	4.27±
			2.2	0.46	77.08	0.41
30	21.48±0.48	1014±	73.2±	15.95±	5266.14±	3.63±
		15	1.1	0.29	68.36	0.37
35	22.19±0.42	970±	67.0±	14.42±	1097.11±	4.25±
		18	2.4	0.36	40.86	0.46
40	20.39±0.71	978±9	68.1±	13.58±	1727.06±	4.01±
			2.4	0.38	15.67	0.54



**Figure S3.** Time evolution of photovoltaic parameters of devices fabricated with or without PTB7 spacer.



**Figure S4.** EDS spectra of CuSCN surface without (a) and (b) with PTB7 spacer.



**Figure S5.** AFM images of perovskite surface treated with different processes.

**Table S2.** Analyzed parameters of PbI<sub>2</sub> (001) and perovskite (110) diffraction peaks.

	<b>2-Theta</b>	<b>d (Å)</b>	<b>Height</b>	<b>I%</b>	<b>Area</b>	<b>I%</b>	<b>FWHM</b>
PVK	12	7.0084	1635	251	29917	207	0.311
	14	6.3657	650	100	14492	100	0.379
PVK+DSE	12	6.9975	2054	417	37224	329	0.308
	14	6.3569	492	100	11327	100	0.391
PVK+PTAA+DES	12	7.0083	1899	253	35404	214	0.317
	14	6.3658	751	100	16535	100	0.374

**Table S3.** Statistical photovoltaic parameters of devices fabricated with different rpm of PTAA.

<b>PTAA spin speed (rpm)</b>	<b>Jsc (mA/cm<sup>2</sup>)</b>	<b>Voc (mV)</b>	<b>FF (%)</b>	<b>PCE (%)</b>	<b>Rsh (Ωcm<sup>2</sup>)</b>	<b>Rs (Ωcm<sup>2</sup>)</b>
Null	21.49±0.41	1012±	73.2±	15.91±	3999.44±	3.76±
		16	1.1	0.28	32.01	0.46
2000	21.79±0.28	1020±1	73.8±	16.41±	3459.95±	3.43±
			0.8	0.21	30.20	0.15
3000	21.56±0.58	1020±1	73.8±	16.23±	3473.06±	3.47±
			0.9	0.53	22.57	0.25
4000	23.11±0.42	1024±	74.5±	17.63±	3291.62±	3.22±
		22	1.4	0.39	27.18	0.46
5000	21.85±0.86	1012±	73.5±	16.23±	6676.02±	3.27±
		16	1.7	0.32	10.08	0.44